

L Number	Hits	Search Text	DB	Time stamp
1	53572	((oxidis\$3 oxidiz\$3 oxidation) near15 (silicon si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/11 13:36
8	7	((oxidis\$3 oxidiz\$3 oxidation) near15 (silicon si)) and (viscoelastic near5 temperature)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/11 13:41
15	459	((oxidis\$3 oxidiz\$3 oxidation) near15 (silicon si)) and (glass adj transition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/11 13:42
22	15	((oxidis\$3 oxidiz\$3 oxidation) near15 (silicon si)) same (glass adj transition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/11 13:42
29	33	(gate adj2 (dielectric oxide dioxide insulat\$4)) same (((Fig. figure drawing figs.) near20 (oxidation oxidiz\$3 oxidis\$3 RTO (rapid adj thermal adj oxidation)) near20 (method process steps recipe)) ((plot\$4 graph\$3) near20 (oxidation oxidiz\$3 oxidis\$3 RTO (rapid adj thermal adj oxidation)) near20 (method process steps recipe)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/11 13:49